

## N-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ)
12	0.0053 at V <sub>GS</sub> = 4.5 V	21.5	29.5 nC
	0.006 at V <sub>GS</sub> = 2.5 V	20.2	
	0.0074 at V <sub>GS</sub> = 1.8 V	18.2	

### FEATURES

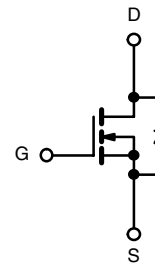
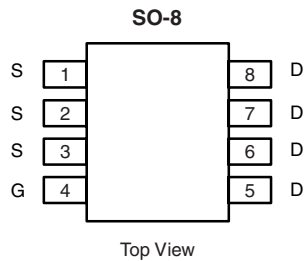
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested



**RoHS**  
COMPLIANT

### APPLICATIONS

- Synchronous Rectifier
- Point-of-Load Synchronous Buck Converter



Ordering Information: Si4866BDY-T1-E3 (Lead (Pb)-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	12	V
Gate-Source Voltage	V <sub>GS</sub>	± 8	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	A
		T <sub>C</sub> = 70 °C	
		T <sub>A</sub> = 25 °C	
		T <sub>A</sub> = 70 °C	
Pulsed Drain Current	I <sub>DM</sub>	50	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	4.0
		T <sub>A</sub> = 25 °C	2.3 <sup>b,c</sup>
Single Pulse Avalanche Current	I <sub>AS</sub>	20	
Avalanche Energy	E <sub>AS</sub>	20	mJ
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	W
		T <sub>C</sub> = 70 °C	
		T <sub>A</sub> = 25 °C	
		T <sub>A</sub> = 70 °C	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b,d</sup>	R <sub>thJA</sub>	40	50	°C/W	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	23	28		

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 sec.
- Maximum under Steady State conditions is 90 °C/W.

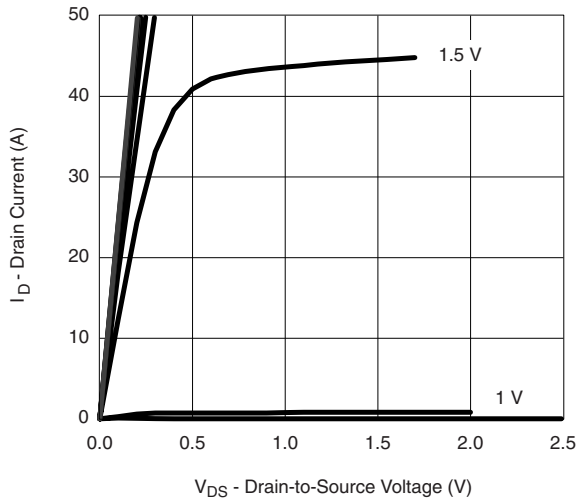
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	12			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		12		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 3.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.4		1.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 12\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 12\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 4.5\text{ V}$	20			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 12\text{ A}$		0.0042	0.0053	$\Omega$
		$V_{GS} = 2.5\text{ V}, I_D = 10\text{ A}$		0.0048	0.0060	
		$V_{GS} = 1.8\text{ V}, I_D = 8\text{ A}$		0.006	0.0074	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 12\text{ A}$		80		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 6\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		5020		pF
Output Capacitance	$C_{oss}$			1305		
Reverse Transfer Capacitance	$C_{rss}$			805		
Total Gate Charge	$Q_g$	$V_{DS} = 6\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$		52	80	nC
			$V_{DS} = 6\text{ V}, V_{GS} = 2.5\text{ V}, I_D = 10\text{ A}$		29.5	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 6\text{ V}, V_{GS} = 2.5\text{ V}, I_D = 10\text{ A}$			6.2	
Gate-Drain Charge	$Q_{gd}$			8.9		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		0.8	1.3	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 6\text{ V}, R_L = 1.2\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		26	40	ns
Rise Time	$t_r$			18	30	
Turn-Off Delay Time	$t_{d(off)}$			85	130	
Fall Time	$t_f$			32	50	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 6\text{ V}, R_L = 1.2\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		13	25	
Rise Time	$t_r$			12	24	
Turn-Off Delay Time	$t_{d(off)}$			57	90	
Fall Time	$t_f$			9	18	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			4	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				50	
Body Diode Voltage	$V_{SD}$	$I_S = 2.3\text{ A}$		0.62	1.1	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 9.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		50	80	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			35	55	nC
Reverse Recovery Fall Time	$t_a$			19		ns
Reverse Recovery Rise Time	$t_b$			31		

Notes:

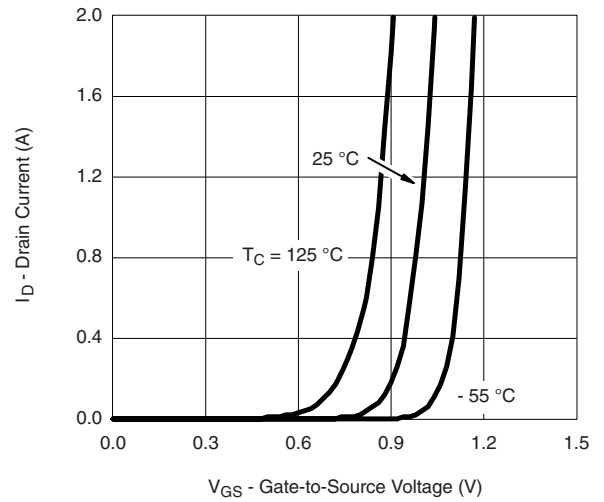
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

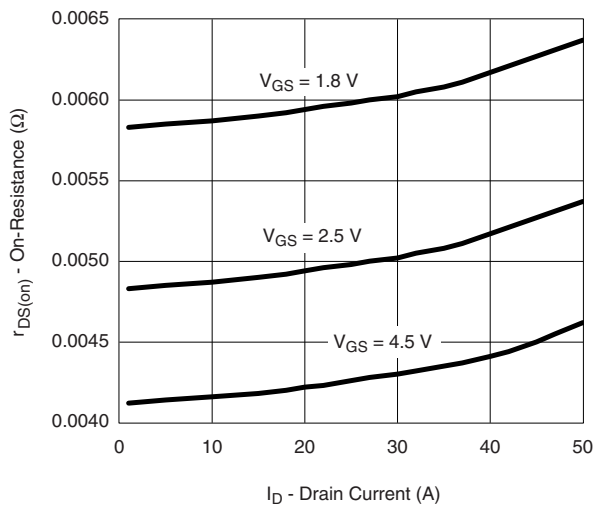
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



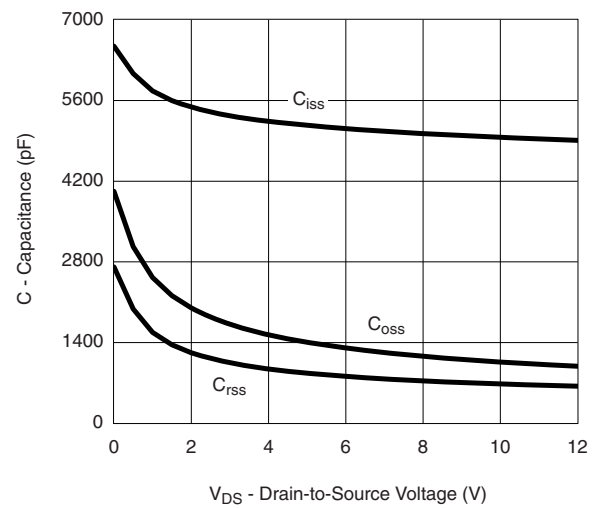
**Output Characteristics**



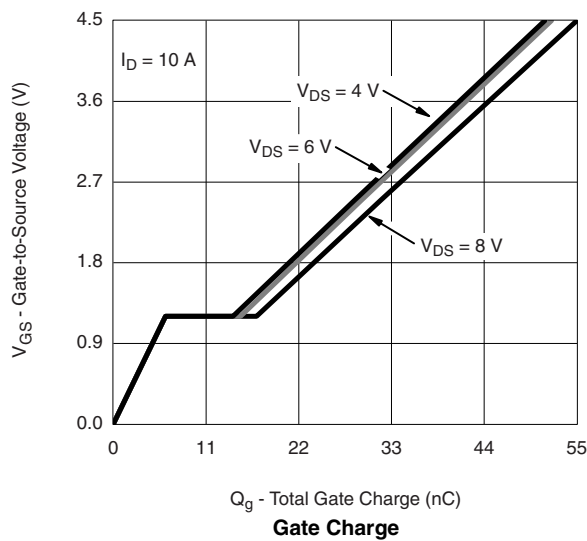
**Transfer Characteristics**



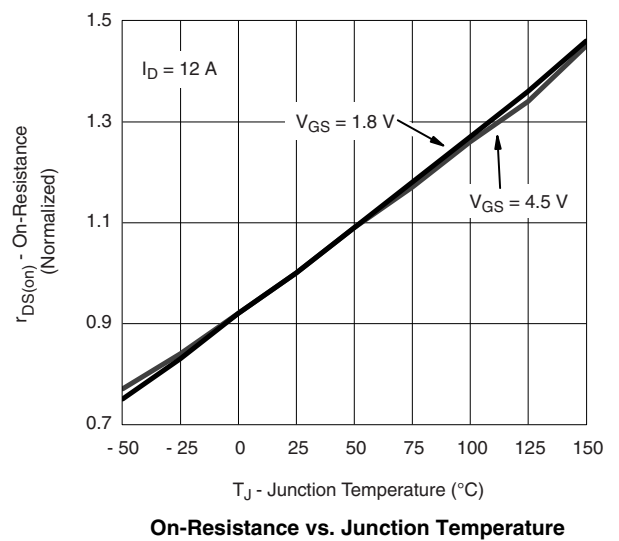
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



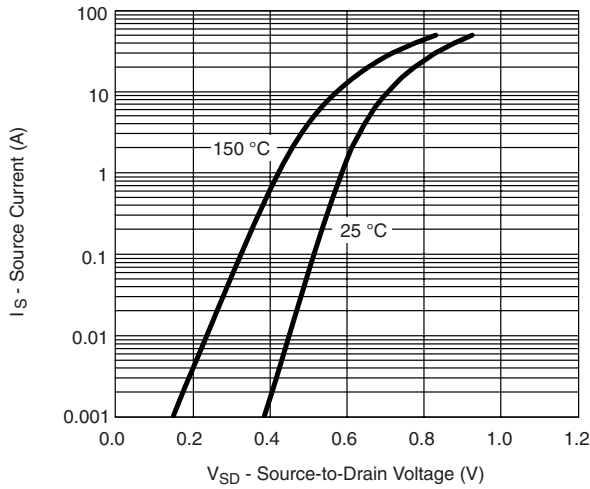
**Gate Charge**



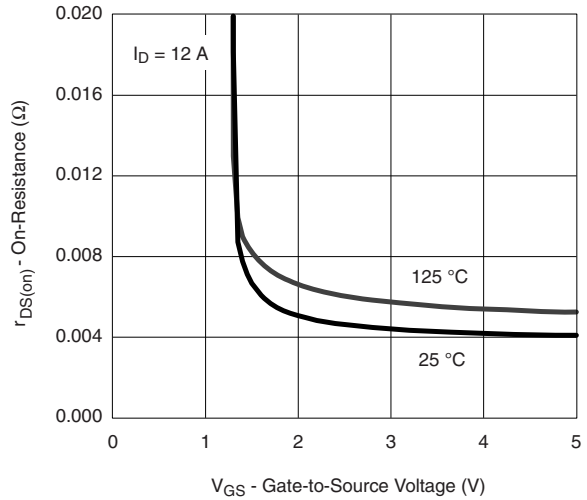
**On-Resistance vs. Junction Temperature**



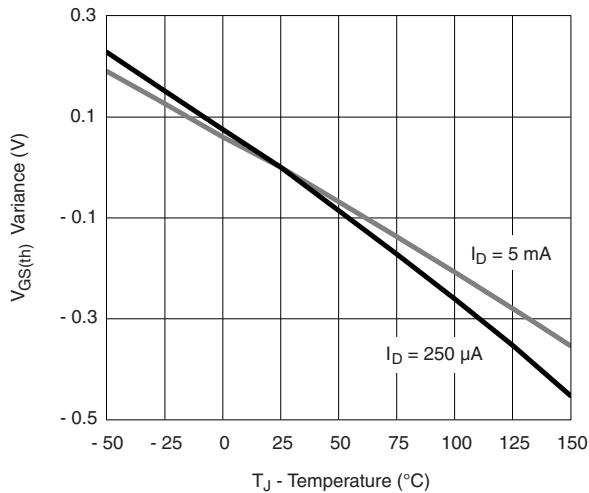
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



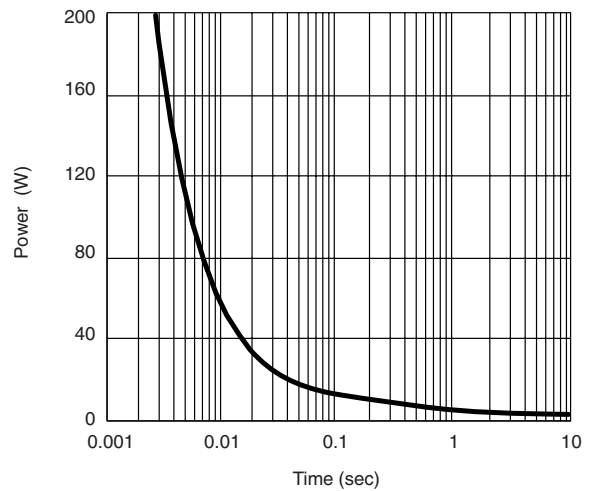
**Source-Drain Diode Forward Voltage**



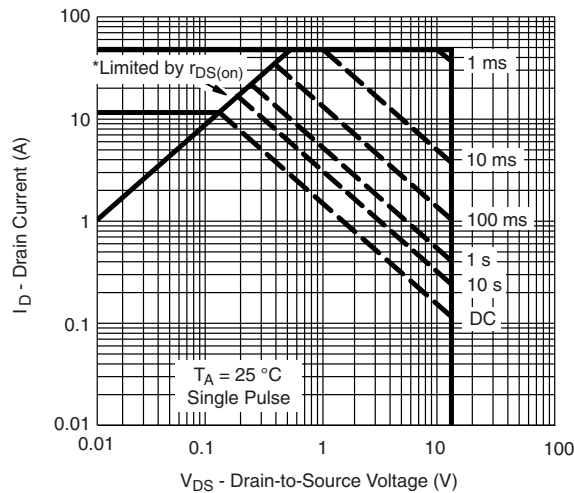
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



**Single Pulse Power, Junction-to-Ambient**

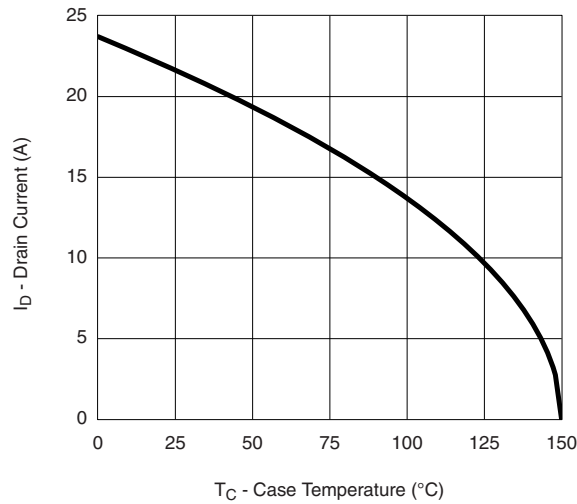


\* $V_{GS} >$  minimum  $V_{GS}$  at which  $r_{DS(on)}$  is specified

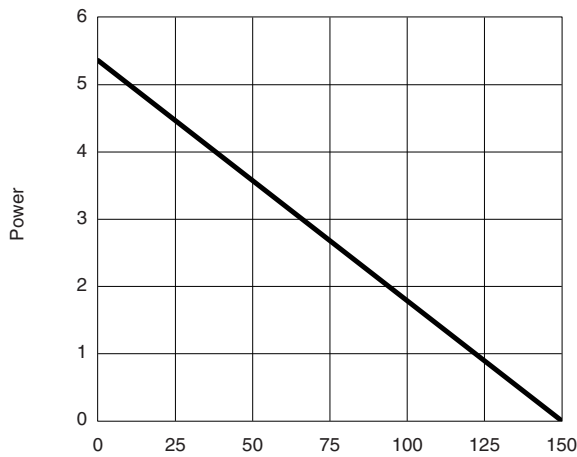
**Safe Operating Area, Junction-to-Ambient**



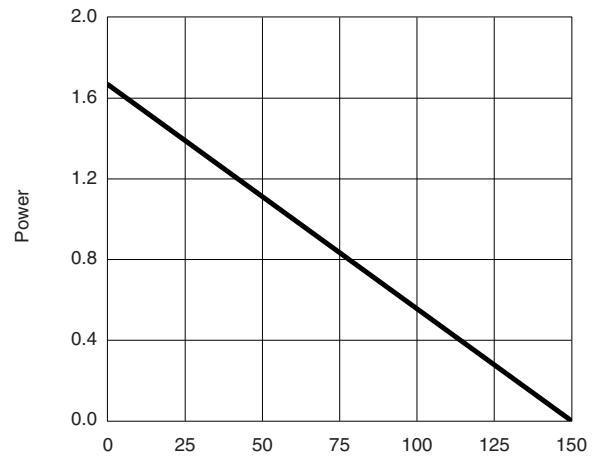
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Current Derating\***



**Power, Junction-to-Foot**

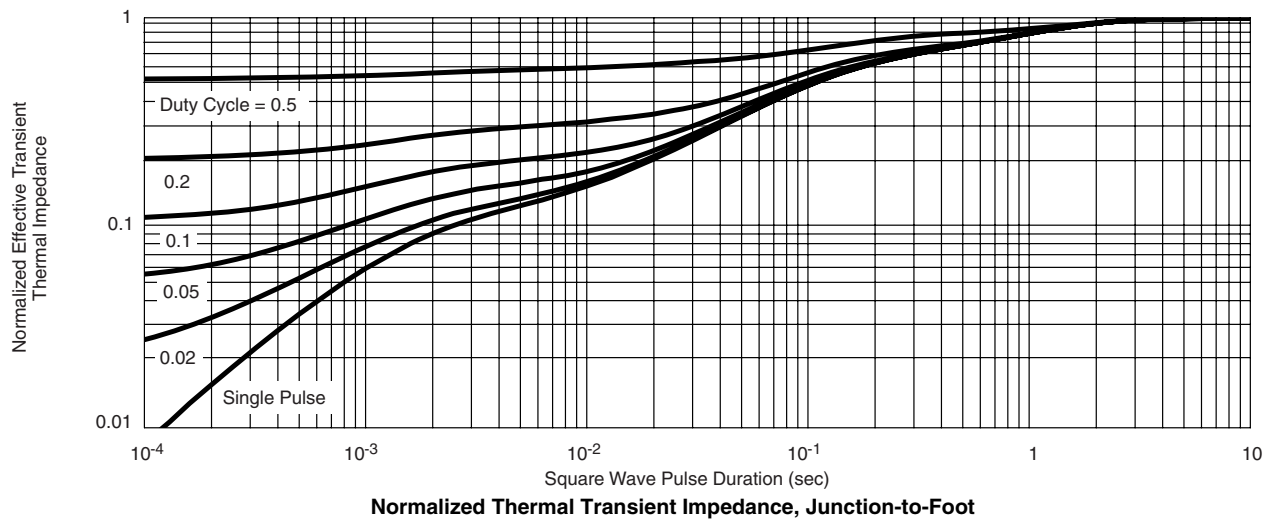
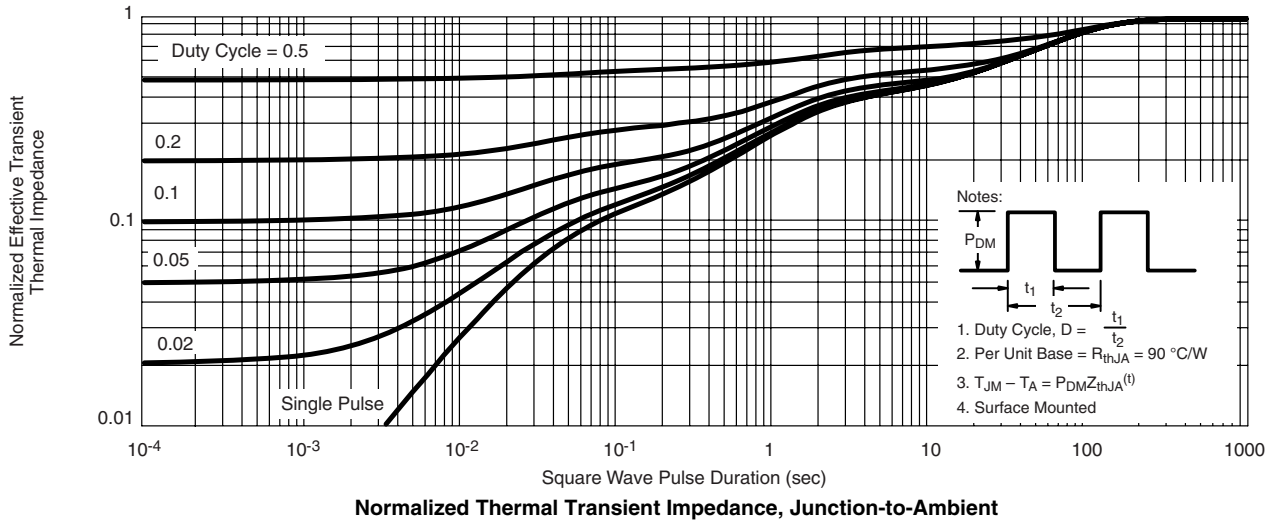


**Power, Junction-to-Ambient**

\*The power dissipation  $P_D$  is based on  $T_{J(max)} = 175\text{ °C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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